NEC

MOS FIELD EFFECT TRANSISTOR
2SK3358

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

DESCRIPTION

The 2SK3358 is N-Channel MOS Field Effect Transistor designed for high current switching applications.

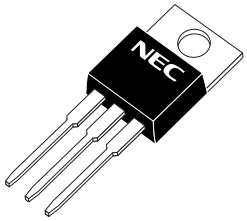
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3358	TO-220AB
2SK3358-S	TO-262
2SK3358-Z	TO-220SMD

FEATURES

- Low on-state resistance
  $R_{DS(on)1}$ = 30 mΩ MAX. (V_{GS} = 10 V, I_D = 28 A)
★ $R_{DS(on)2}$ = 40 mΩ MAX. (V_{GS} = 4.5 V, I_D = 20 A)
★ • Low C_{iss}: C_{iss} = 3200 pF TYP.
- Built-in gate protection diode

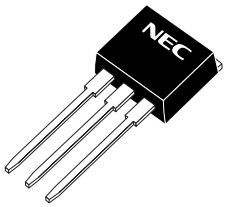
(TO-220AB)



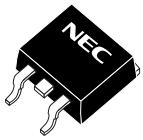
ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	100	V
Gate to Source Voltage (V_{DS} = 0 V)	$V_{GSS(AC)}$	±20	V
Gate to Source Voltage (V_{DS} = 0 V)	$V_{GSS(DC)}$	+20, –10	V
Drain Current (DC)	$I_{D(DC)}$	±55	A
★ Drain Current (Pulse) Note1	$I_{D(pulse)}$	±165	A
Total Power Dissipation (T_C = 25°C)	P_T	100	W
Total Power Dissipation (T_A = 25°C)	P_T	1.5	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C
Single Avalanche Current Note2	I_{AS}	39	A
Single Avalanche Energy Note2	E_{AS}	152	mJ

(TO-262)



(TO-220SMD)



Notes 1. PW ≤ 10 μs, Duty cycle ≤ 1 %

2. Starting T_{ch} = 25 °C, R_G = 25 Ω, V_{GS} = 20 V → 0 V

THERMAL RESISTANCE

Channel to Case	$R_{th(ch-C)}$	1.25	°C/W
Channel to Ambient	$R_{th(ch-A)}$	83.3	°C/W

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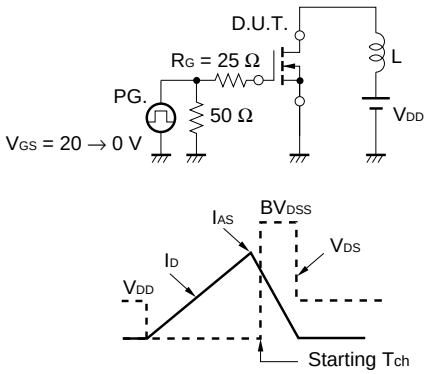
The mark ★ shows major revised points.

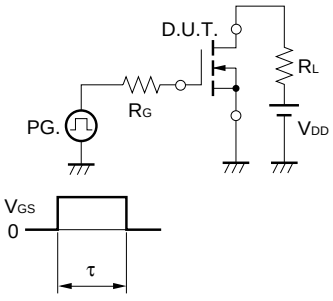
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

	CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
★	Drain to Source On-state Resistance	$R_{DS(on)1}$	V_{GS} = 10 V, I_D = 28 A		20	30	mΩ
★		$R_{DS(on)2}$	V_{GS} = 4.5 V, I_D = 20 A		28	40	mΩ
★	Gate to Source Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 250 μA	1.5	2.0	2.5	V
★	Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = 10 V, I_D = 28 A	17	35		S
	Drain Leakage Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			10	μA
	Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±10	μA
★	Input Capacitance	C_{iss}	V_{DS} = 10 V		3200		pF
	Output Capacitance	C_{oss}	V_{GS} = 0 V		640		pF
	Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		360		pF
	Turn-on Delay Time	$t_{d(on)}$	I_D = 28 A		40		ns
	Rise Time	t_r	$V_{GS(on)}$ = 10 V		300		ns
	Turn-off Delay Time	$t_{d(off)}$	V_{DD} = 50 V		220		ns
	Fall Time	t_f	R_G = 10 Ω		230		ns
	Total Gate Charge	Q_G	I_D = 55 A		84		nC
	Gate to Source Charge	Q_{GS}	V_{DD} = 80		11		nC
	Gate to Drain Charge	Q_{GD}	$V_{GS(on)}$ = 10 V		31		nC
	Body Diode Forward Voltage	$V_{F(S-D)}$	I_F = 55 A, V_{GS} = 0 V		1.0		V
	Reverse Recovery Time	t_{rr}	I_F = 55 A, V_{GS} = 0 V		160		ns
	Reverse Recovery Charge	Q_{rr}	di/dt = 100 A/μs		760		nC

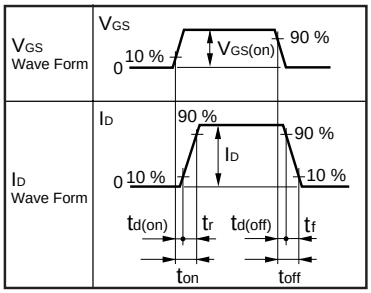
TEST CIRCUIT 1 AVALANCHE CAPABILITY



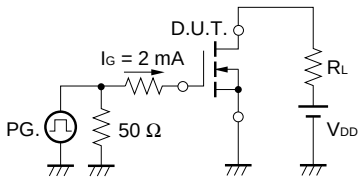
TEST CIRCUIT 2 SWITCHING TIME



τ = 1 μs
Duty Cycle ≤ 1 %

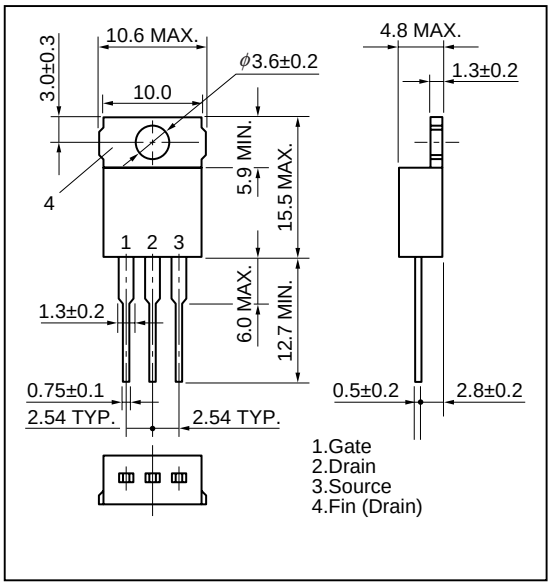


TEST CIRCUIT 3 GATE CHARGE

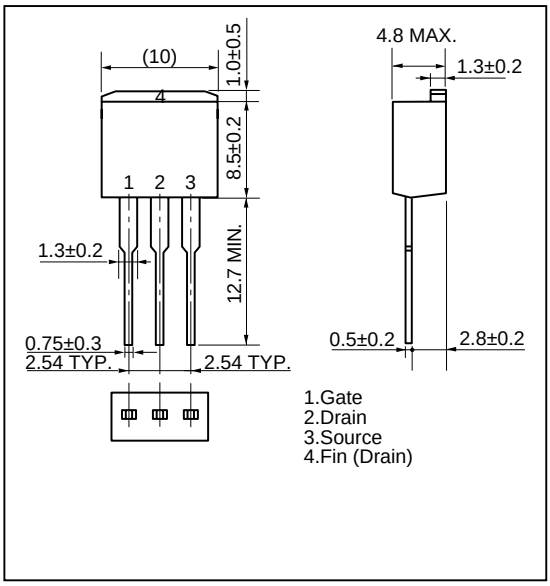


PACKAGE DRAWINGS (Unit : mm)

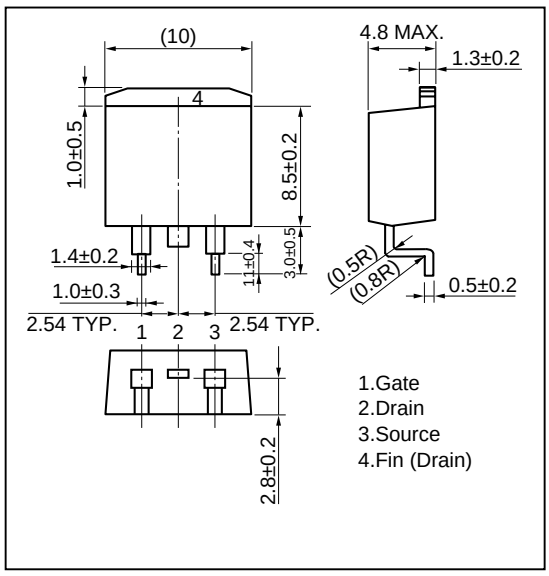
1)TO-220AB (MP-25)



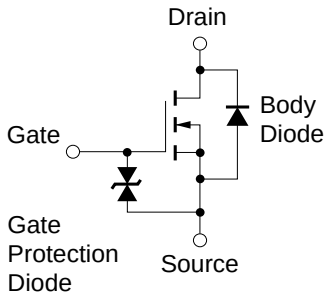
2)TO-262 (MP-25 Fin Cut)



3)TO-220SMD (MP-25Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.